

**GreenPAK** ™

### **RZ/T2H Power Sequencer with IIC**

#### **General Description**

Renesas SLG7RN46899 is a low power and small form device. The SoC is housed in a 1.6mm x 2.0mm STQFN package which is optimal for using with small devices.

#### **Features**

- Low Power Consumption
- Pb Free / RoHS Compliant
- Halogen Free
- STQFN 14 Package

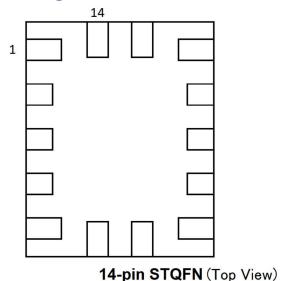
### **Output Summary**

5 Outputs - Push Pull 1X

#### Pin name

Pin name	Pin#	Pin name
VDD	8	GND
5V_Q	9	NC
SCL	10	RESET#
SDA	11	GATE_D
NC	12	GATE_C
NC	13	GATE_B
NC	14	GATE_A#
	VDD 5V_Q SCL SDA NC	VDD     8       5V_Q     9       SCL     10       SDA     11       NC     12       NC     13

### **Pin Configuration**



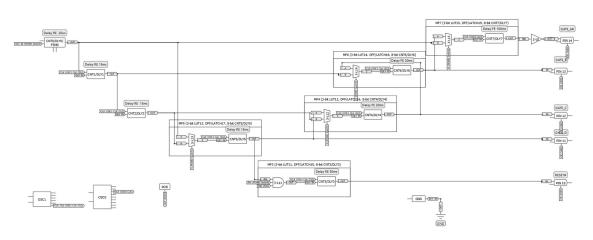


# **RZ/T2H Power Sequencer with IIC**

### **Block Diagram**









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**Pin Configuration** 

Pin#	Pin Name	Туре	Pin Description	Internal Resistor
1	VDD	PWR	Supply Voltage	
2	5V_Q	Digital Input	Digital Input without Schmitt trigger	1MΩ pulldown
3	SCL	Digital Input	Digital Input without Schmitt trigger	floating
4	SDA	Digital Input	Digital Input without Schmitt trigger	floating
5	NC		Keep Floating or Connect to GND	
6	NC		Keep Floating or Connect to GND	
7	NC		Keep Floating or Connect to GND	
8	GND	GND	Ground	
9	NC		Keep Floating or Connect to GND	
10	RESET#	Digital Output	Push Pull 1X	floating
11	GATE_D	Digital Output	Push Pull 1X	floating
12	GATE_C	Digital Output	Push Pull 1X	floating
13	GATE_B	Digital Output	Push Pull 1X	floating
14	GATE_A#	Digital Output	Push Pull 1X	floating

**Ordering Information** 

Part Number	Package Type
SLG7RN46899V	14-pin STQFN - Tape and Reel (3k units)



### **Absolute Maximum Conditions**

Parameter	Min.	Max.	Unit
V <sub>HIGH</sub> to GND	-0.3	7	V
Voltage at Input Pin	GND-0.5V	V <sub>DD</sub> +0.5V	V
Maximum Average or DC Current (Through V <sub>DD</sub> or GND pin)		90	mA
Maximum Average or DC Current (Through pin)   Push-Pull 1x		11	mA
Current at Input Pin	-1.0	1.0	mA
Input leakage Current (Absolute Value)		1000	nA
Storage Temperature Range	-65	150	°C
Junction Temperature		150	°C
ESD Protection (Human Body Model)	2000		V
ESD Protection (Charged Device Model)	1300		V
Moisture Sensitivity Level	1		

### **Electrical Characteristics**

Symbol	Parameter	Condition/Note	Min.	Тур.	Max.	Unit
$V_{DD}$	Supply Voltage		2.3	5	5.5	V
TA	Operating Temperature		-40	25	85	°C
C <sub>VDD</sub>	Capacitor Value at VDD		0.1			μF
Cin	Input Capacitance			4		pF
ΙQ	Quiescent Current	Static inputs and floating outputs. PIN3, PIN4 are HIGH		1		μA
Vo	Maximal Voltage Applied to any PIN in High- Impedance State				VDD+0.3	V
ViH	HIGH-Level Input Voltage	Logic Input (Note 1)	0.7xVDD		VDD+0.3	V
VIL	LOW-Level Input Voltage	Logic Input (Note 1)	GND-0.3		0.3xVDD	V
	LIICH Lovel Output	Push-Pull 1X, I <sub>OH</sub> =1mA at VDD=2.5V	2.15			V
Vон	HIGH-Level Output Voltage	Push-Pull 1X, I <sub>OH</sub> =3mA at VDD=3.3V	2.7			V
	Voltage	Push-Pull 1X, I <sub>OH</sub> =5mA at VDD=5.0V	4.16			V
	LOW-Level Output	Push-Pull 1X, IoL=1mA, at VDD=2.5V			0.103	V
Vol	Voltage	Push-Pull 1X, IoL=3mA, at VDD=3.3V			0.218	V
	Voltage	Push-Pull 1X, IoL=5mA, at VDD=5.0V			0.270	V
	HIGH-Level Output	Push-Pull 1X, V <sub>OH</sub> =VDD-0.2V at VDD=2.5V	1.37			mA
Іон	Current (Note 2)	Push-Pull 1X, V <sub>OH</sub> =2.4V at VDD=3.3V	5.61			mA
	, ,	Push-Pull 1X, V <sub>OH</sub> =2.4V at VDD=5.0V	20.42			mA
	LOW Love Control	Push-Pull 1X, V <sub>OL</sub> =0.15V, at VDD=2.5V	1.52			mA
$I_{OL}$	LOW-Level Output	Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=3.3V	5.42			mA
	Current (Note 2)	Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=5.0V	7.36			mA
R <sub>PULL_DOWN</sub>	Internal Pull Down Resistance	Pull down on PIN 2		1		МΩ
<b>T</b>	Dalay O Time	At temperature 25°C	20	21	24	μs
T <sub>DLY0</sub>	Delay0 Time	At temperature -40 +85°C (Note 3)	20	21	27	μs
<b>T</b>	Delevit Time	At temperature 25°C	14.81	15.12	15.46	ms
T <sub>DLY1</sub>	Delay1 Time	At temperature -40 +85°C (Note 3)	14.76	15.12	15.66	ms
Т	Dolov? Time	At temperature 25°C	14.81	15.12	15.46	ms
T <sub>DLY2</sub>	Delay2 Time	At temperature -40 +85°C (Note 3)	14.76	15.12	15.66	ms
Т	Dolov2 Time	At temperature 25°C	49.38	50.12	50.94	ms
T <sub>DLY3</sub>	Delay3 Time	At temperature -40 +85°C (Note 3)	49.22	50.12	51.57	ms



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Т	Dolov4 Time	At temperature 25°C	19.75	20.12	20.53	ms
T <sub>DLY4</sub>	Delay4 Time	At temperature -40 +85°C (Note 3)	19.69	20.12	20.79	ms
Т	Deleve Time	At temperature 25°C	14.81	15.12	15.46	ms
T <sub>DLY5</sub>	Delay5 Time	At temperature -40 +85°C (Note 3)	14.76	15.12	15.66	ms
т	Delevis Time	At temperature 25°C	29.63	30.12	30.67	ms
I DLY6	T <sub>DLY6</sub> Delay6 Time	At temperature -40 +85°C (Note 3)	29.53	30.12	31.05	ms
т	Delay7 Time	At temperature 25°C	99.02	100.34	102.56	ms
T <sub>DLY7</sub>		At temperature -40 +85°C (Note 3)	97.95	100.34	109.66	ms
Tsu	Startup Time	From VDD rising past PON <sub>THR</sub>		1	2	ms
PONTHR	Power On Threshold	V <sub>DD</sub> Level Required to Start Up the Chip	1.6	1.85	2.05	<
POFFTHR	Power Off Threshold	V <sub>DD</sub> Level Required to Switch Off the Chip	0.85	1.25	1.5	٧

Note 1 No hysteresis.

Note 2 DC or average current through any pin should not exceed value given in Absolute Maximum Conditions.

Note 3 Guaranteed by Design.

### I<sup>2</sup>C Specifications

Symbol	Parameter	Condition/Note	Min.	Тур.	Max.	Unit
F <sub>SCL</sub>	Clock Frequency, SCL	$V_{DD} = (2.35.5) V$			400	kHz
$t_{LOW}$	Clock Pulse Width Low	$V_{DD} = (2.35.5) V$	1300			ns
t <sub>HIGH</sub>	Clock Pulse Width High	$V_{DD} = (2.35.5) V$	600			ns
	Input Filter Spike	$V_{DD} = 2.5V \pm 8\%$			95	ns
$t_l$	Suppression (SCL, SDA)	$V_{DD} = 3.3V \pm 10\%$			95	ns
	Suppression (SCL, SDA)	$V_{DD} = 5.0V \pm 10\%$			111	ns
t <sub>AA</sub>	Clock Low to Data Out Valid	V <sub>DD</sub> = (2.35.5) V			900	ns
t <sub>BUF</sub>	Bus Free Time between Stop and Start	V <sub>DD</sub> = (2.35.5) V	1300			ns
thd_sta	Start Hold Time	$V_{DD} = (2.35.5) V$	600			ns
tsu_sta	Start Set-up Time	$V_{DD} = (2.35.5) V$	600			ns
thd_dat	Data Hold Time	$V_{DD} = (2.35.5) V$	0			ns
tsu_dat	Data Set-up Time	$V_{DD} = (2.35.5) V$	100			ns
<b>t</b> R	Inputs Rise Time	$V_{DD} = (2.35.5) V$			300	ns
t⊧	Inputs Fall Time	$V_{DD} = (2.35.5) V$			300	ns
tsu_sto	Stop Set-up Time	$V_{DD} = (2.35.5) V$	600			ns
t <sub>DH</sub>	Data Out Hold Time	V <sub>DD</sub> = (2.35.5) V	50			ns
Note 1 Tim	ing diagram can be found in	the Figure 2.				

### **Chip address**

Omp ad	GII O O O	
HEX	BIN	DEC
0x08	0001000	8



### **I2C Description**

#### 1. I2C Basic Command Structure

Each command to the I2C Serial Communications block begins with a Control Byte. The bits inside this Control Byte are shown in Figure 1. After the Start bit, the first four bits are a control code, which can be set by the user in reg<2027:2024>. The Block Address is the next three bits (A10, A9, A8), which will define the most significant bits in the addressing of the data to be read ("1") or written ("0") by the command. This Control Byte will be followed by an Acknowledge bit (ACK).

With the exception of the Current Address Read command, all commands will have the Control Byte followed by the Word Address. The Word Address, in conjunction with the three address bits in the Control Byte, will define the specific data byte to be read or written in the command. Figure 1 shows this basic command structure.

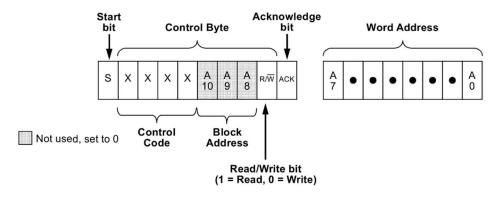


Figure 1. I2C Basic Command Structure

#### 2. I2C Serial General Timing

Shown in Figure 2 is the general timing characteristics for the I2C Serial Communications block.

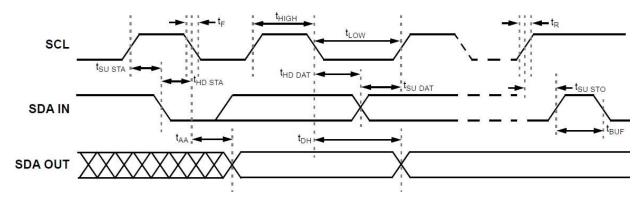


Figure 2. I2C Serial General Timing



#### 3. I2C Serial Communications: Read and Write Commands

Following the Start condition from the master, the Control Code [4 bits], the block address [3 bits] and the R/W bit (set to "0"), is placed onto the bus by the Bus Master. After the I2C Serial Communications block has provided an Acknowledge bit (ACK) the next byte transmitted by the master is the Word Address. The Block Address is the next three bits, and is the higher order addressing bits (A10, A9, A8), which when added to the Word Address will together set the internal address pointer in the SLG7RN46899 to the correct data byte to be written. After the SLG7RN46899 sends another Acknowledge bit, the Bus Master will transmit the data byte to be written into the addressed memory location. The SLG7RN46899 again provides an Acknowledge bit and then the Bus Master generates a Stop condition. The internal write cycle for the data will take place at the time that the SLG7RN46899 generates the Acknowledge bit.

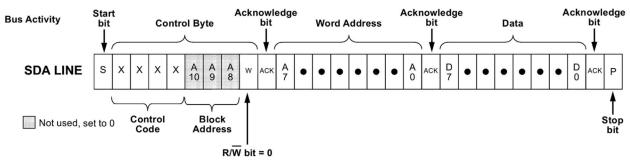


Figure 3. I2C Write Command

The Random Read command starts with a Control Byte (with  $R/\overline{W}$  bit set to "0", indicating a write command) and Word Address to set the internal byte address, followed by a Start bit, and then the Control Byte for the read (exactly the same as the Byte Write command). The Start bit in the middle of the command will halt the decoding of a Write command, but will set the internal address counter in preparation for the second half of the command. After the Start bit, the Bus Master issues a second control byte with the  $R/\overline{W}$  bit set to "1", after which the SLG7RN46899 issues an Acknowledge bit, followed by the requested eight data bits.

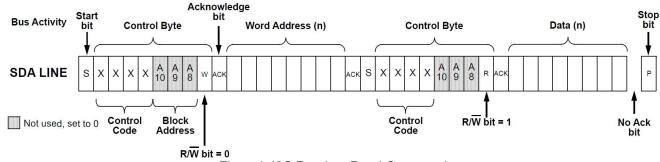
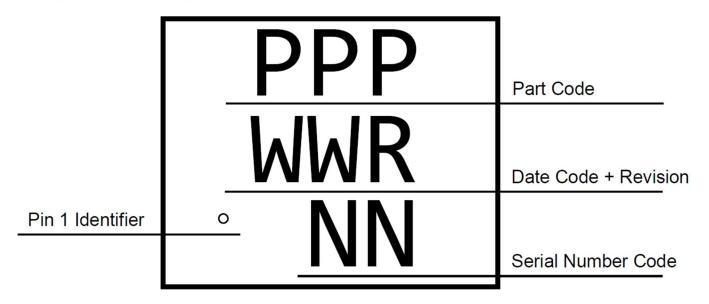


Figure 4. I2C Random Read Command



### **Package Top Marking**



Datasheet Revision	Programming Code Number		Checksum	Part Code	Revision	Date
0.12	001	U	0xE030C08D	1EH		11/06/2024

Lock coverage for this part is indicated by  $\sqrt{\ }$ , from one of the following options:

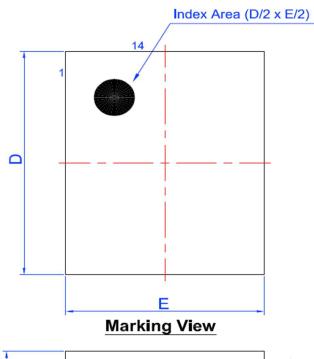
 Unlocked
Partly lock read (mode 1)
Partly lock read2 (mode 2)
Partly lock read2/write (mode 3)
All lock read (mode 4)
All lock write (mode 5)
All lock read/write (mode 6)

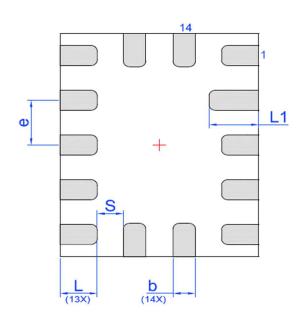
The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.

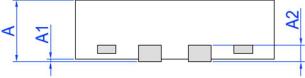


### **Package Outlines**

# STQFN 14L 1.6 x 2.0 x 0.55 mm 0.4P FC Package IC Net Weight: 0.0045 g







### **Marking View**

#### Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
Α	0.50	0.55	0.60	D	1.95	2.00	2.05
A1	0.005	_	0.050	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.25	0.30	0.35
b	0.13	0.18	0.23	L1	0.35	0.40	0.45
е	0.40 BSC			S		0.21 REF	

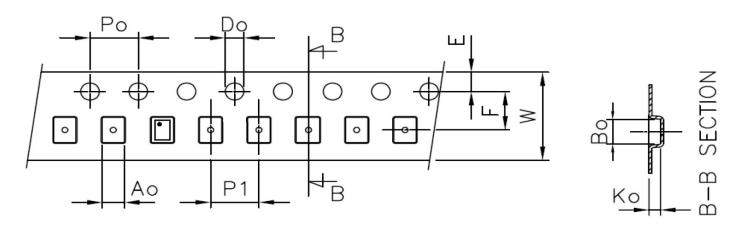


### **Tape and Reel Specification**

	# of Package	Nominal	nal Max Units		Reel & Hub	Leade	Leader (min)		Trailer (min)		Part
		Package Size [mm]	per Reel	per Box	Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STQFN 14L 1.6x2mm 0.4P FC Green	14	1.6x2.0x0.55	3000	3000	178 / 60	100	400	100	400	8	4

**Carrier Tape Drawing and Dimensions** 

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	В0	K0	P0	P1	D0	E	F	W
STQFN 14L 1.6x2 mm 0.4P FC Green	1.9	2.3	0.76	4	4	1.5	1.75	3.5	8



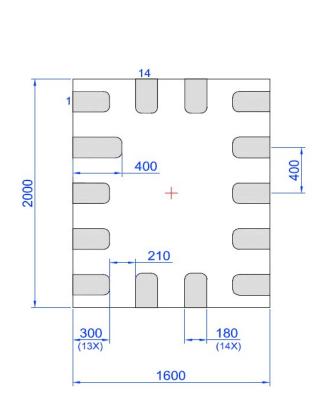
### **Recommended Reflow Soldering Profile**

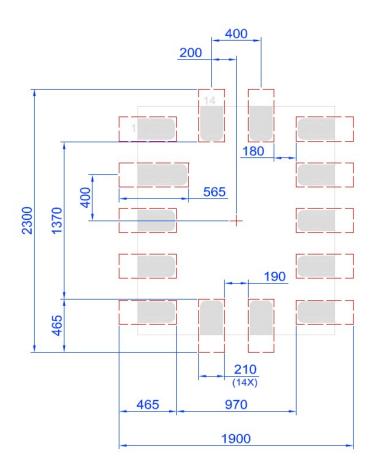
Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 2.64 mm<sup>3</sup> (nominal) for STQFN 14L Package. More information can be found at <a href="https://www.jedec.org">www.jedec.org</a>.



# **RZ/T2H Power Sequencer with IIC**

### **Layout Guidelines**





Unit: um



# **RZ/T2H Power Sequencer with IIC**

### **Datasheet Revision History**

Date	Version	Change	
09/06/2023	0.10	New design	
09/12/2023	0.11	Updated Revision Table	
11/06/2024	0.12	Customer project name changed	

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TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

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